



STB14NM50N, STD14NM50N STF14NM50N, STP14NM50N

N-channel 500 V, 0.28 Ω , 12 A MDmesh™ II Power MOSFET
in DPAK, D²PAK, TO-220 and TO-220FP

Features

Type	V _{DSS} @ T _{Jmax}	R _{DS(on)} max	I _D
STB14NM50N			
STD14NM50N	550 V	< 0.32 Ω	12 A
STF14NM50N			
STP14NM50N			

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

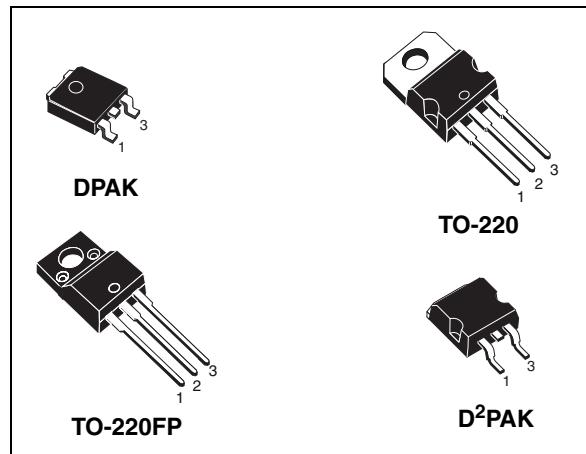
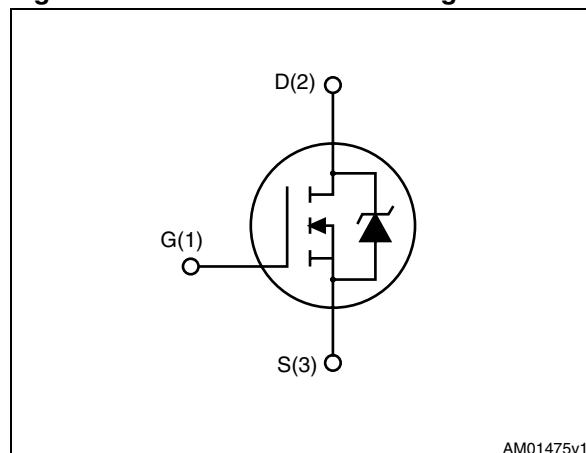


Figure 1. Internal schematic diagram



AM01475v1

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB14NM50N	14NM50N	D ² PAK	Tape and reel
STD14NM50N		DPAK	
STF14NM50N		TO-220FP	Tube
STP14NM50N		TO-220	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220, D ² PAK DPAK	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	500		V
V_{GS}	Gate-source voltage	± 25		V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	12	12 ⁽¹⁾	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	8	8 ⁽¹⁾	A
$I_{DM}^{(2)}$	Drain current (pulsed)	48	48 ⁽¹⁾	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	90	25	W
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	5.5		A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50$ V)	18		mJ
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15		V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1$ s; $T_C = 25^\circ\text{C}$)		2500	V
T_{stg}	Storage temperature	- 55 to 150		°C
T_j	Max. operating junction temperature	150		°C

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 12$ A, $di/dt \leq 400$ A/ μ s, $V_{Peak} < V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value				Unit
		TO-220	DPAK	D ² PAK	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	1.39		5	5	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5			62.5	°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max		50	30		°C/W
T_I	Maximum lead temperature for soldering purpose	300			300	°C

1. When mounted on 1inch² FR-4 board, 2 oz Cu

2 Electrical characteristics

($T_C = 25^\circ\text{C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	500			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}, T_C = 125^\circ\text{C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25 \text{ V}$			0.1	μA
$V_{GS(\text{th})}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 100 \mu\text{A}$	2	3	4	V
$R_{DS(\text{on})}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$		0.28	0.32	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance			816		pF
C_{oss}	Output capacitance	$V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}, V_{GS} = 0$	-	60	-	pF
C_{rss}	Reverse transfer capacitance			3		pF
$C_{oss \text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0 \text{ to } 50 \text{ V}, V_{GS} = 0$	-	307.5	-	pF
R_G	Intrinsic gate resistance	$f = 1 \text{ MHz open drain}$	-	4.5	-	Ω
Q_g	Total gate charge			27		nC
Q_{gs}	Gate-source charge	$V_{DD} = 400 \text{ V}, I_D = 12 \text{ A}, V_{GS} = 10 \text{ V}$ (see Figure 18)	-	4.6	-	nC
Q_{gd}	Gate-drain charge			15		nC

1. $C_{oss \text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400 \text{ V}$, $I_D = 12 \text{ A}$, $R_G = 4.7 \Omega$, $V_{GS} = 10 \text{ V}$ (see Figure 19)	-	10.2	-	ns
t_r	Rise time			16		ns
$t_{d(off)}$	Turn-off-delay time			42		ns
t_f	Fall time			22		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current		-		12	A
	Source-drain current (pulsed)				48	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 12 \text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time	$I_{SD} = 12 \text{ A}$, $dI/dt = 100 \text{ V/ns}$, $V_{DD} = 400 \text{ V}$ (see Figure 22)	-	252		ns
	Reverse recovery charge			2.8		μC
	Reverse recovery current			22		A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time	$I_{SD} = 12 \text{ A}$, $dI/dt = 100 \text{ V/ns}$, $V_{DD} = 400 \text{ V}$, $T_J = 150^\circ\text{C}$ (see Figure 22)	-	300		ns
	Reverse recovery charge			3.3		μC
	Reverse recovery current			22.2		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D²PAK

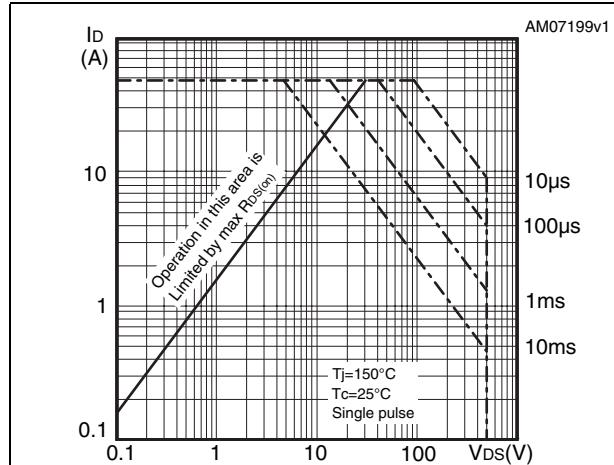


Figure 3. Thermal impedance for TO-220, D²PAK

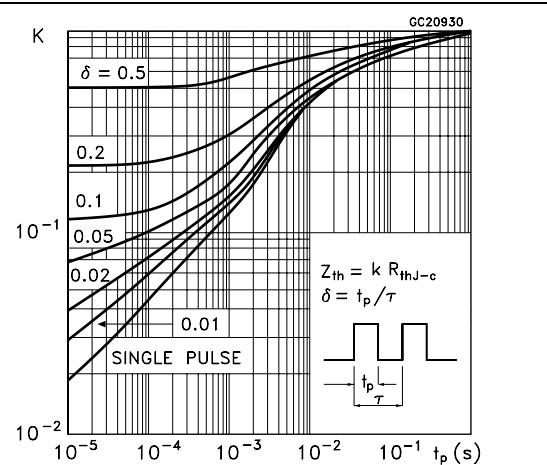


Figure 4. Safe operating area for DPAK

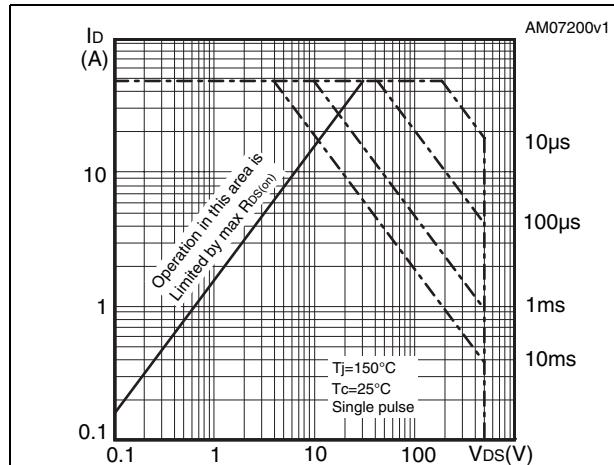


Figure 5. Thermal impedance for DPAK

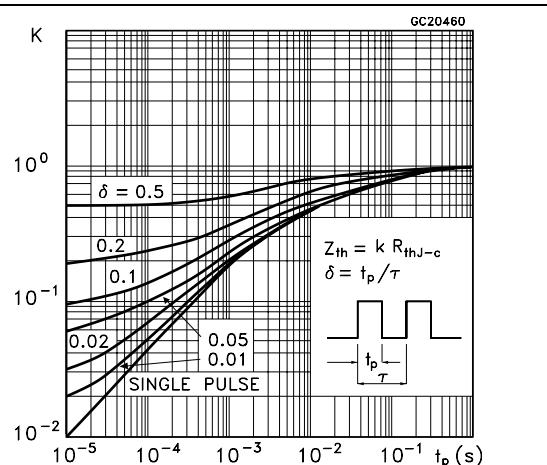


Figure 6. Safe operating area for TO-220FP

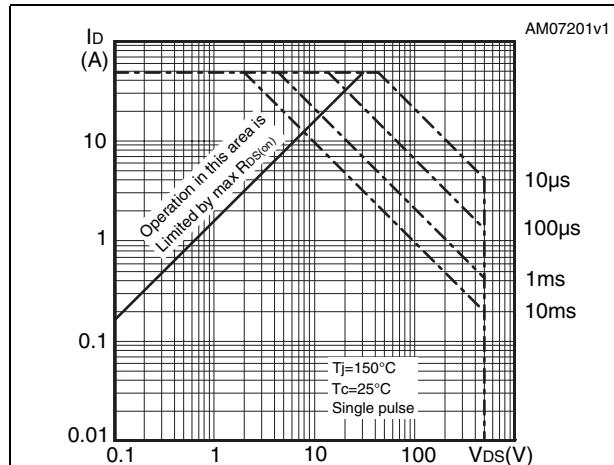


Figure 7. Thermal impedance for TO-220FP

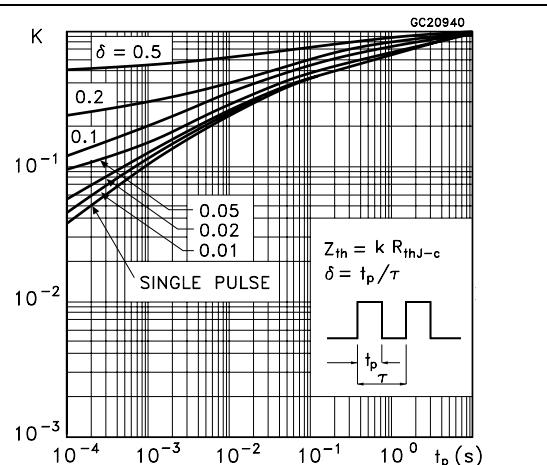


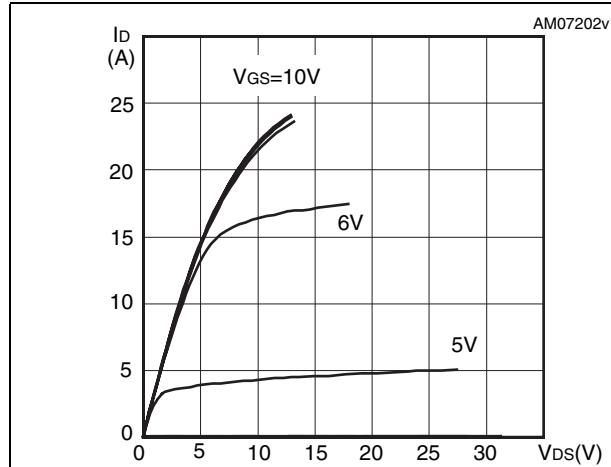
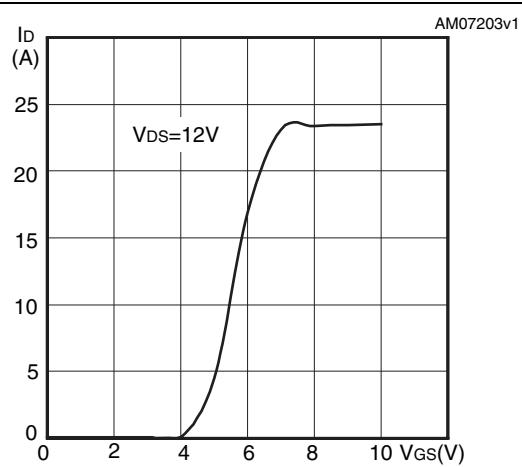
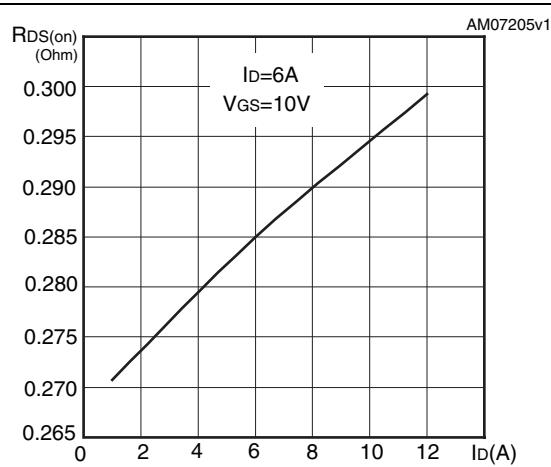
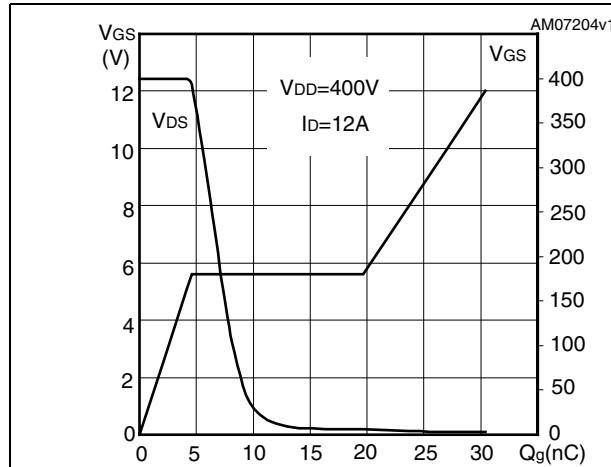
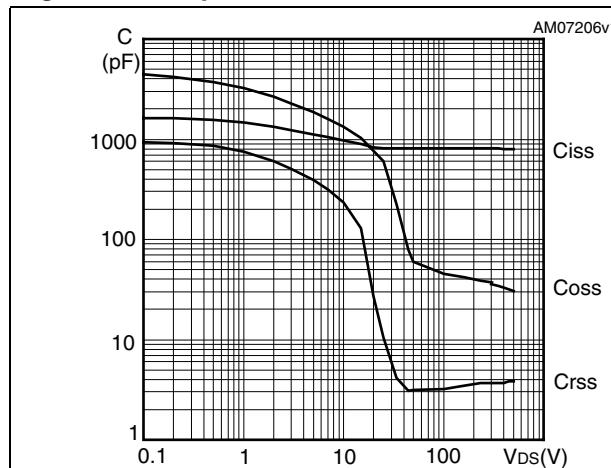
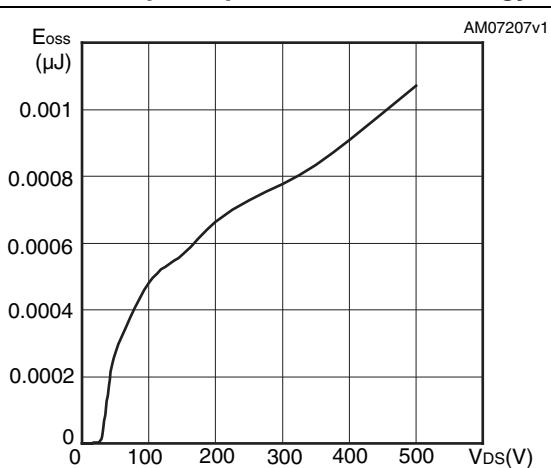
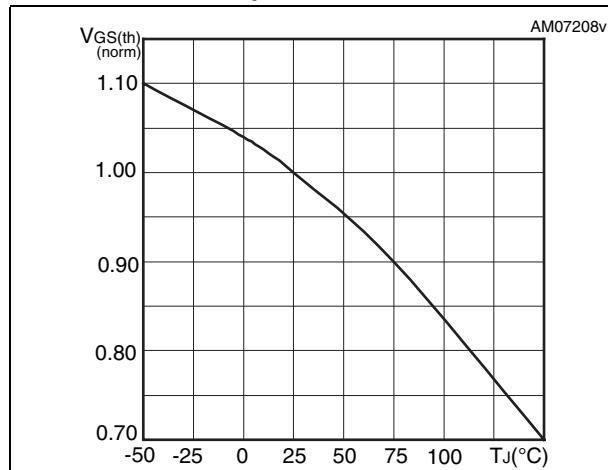
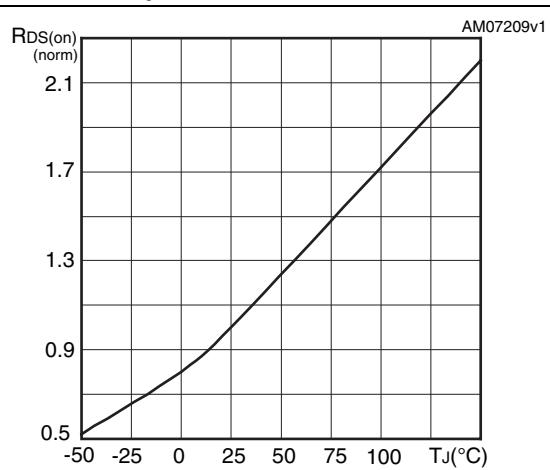
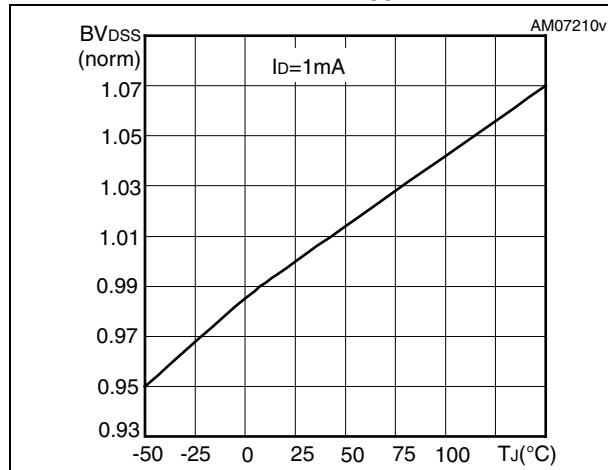
Figure 8. Output characteristics**Figure 9. Transfer characteristics****Figure 10. Gate charge vs gate-source voltage** **Figure 11. Static drain-source on resistance****Figure 12. Capacitance variations****Figure 13. Output capacitance stored energy**

Figure 14. Normalized gate threshold voltage vs temperature**Figure 15. Normalized on resistance vs temperature****Figure 16. Normalized B_{VDSS} vs temperature**

3 Test circuits

Figure 17. Switching times test circuit for resistive load

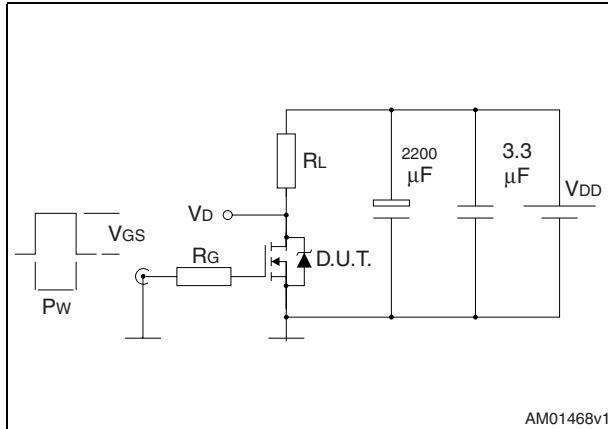


Figure 18. Gate charge test circuit

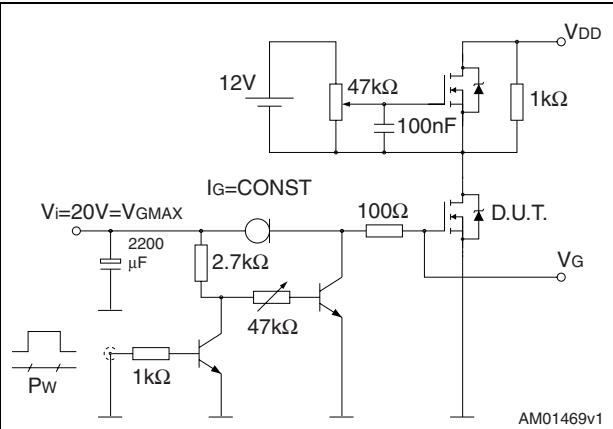


Figure 19. Test circuit for inductive load switching and diode recovery times

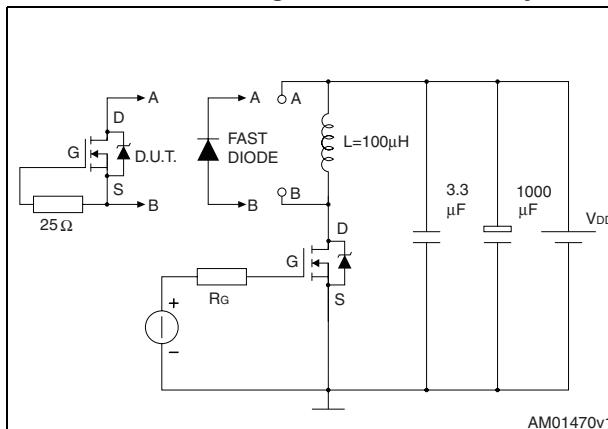


Figure 20. Unclamped inductive load test circuit

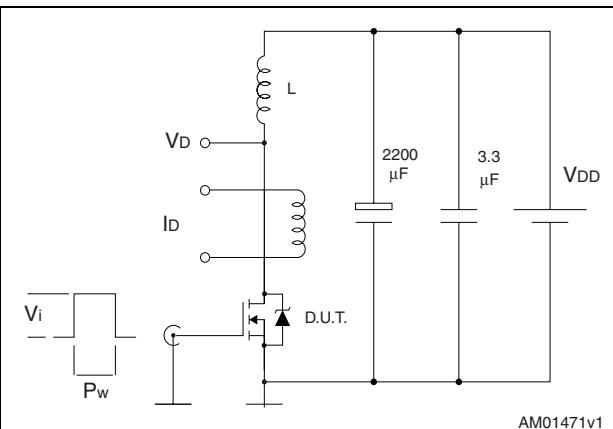


Figure 21. Unclamped inductive waveform

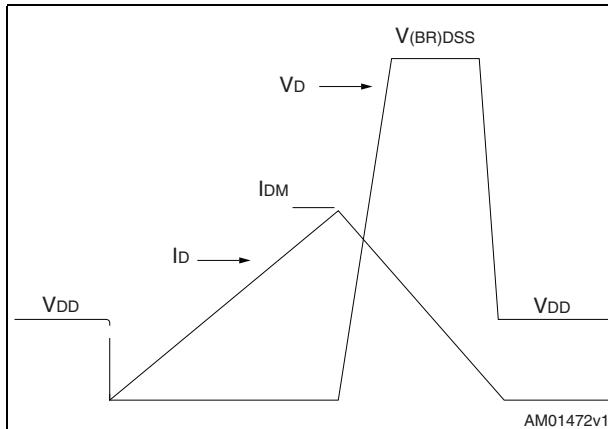
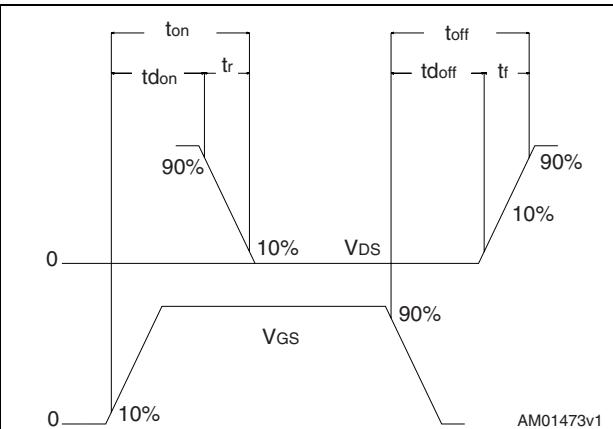


Figure 22. Switching time waveform

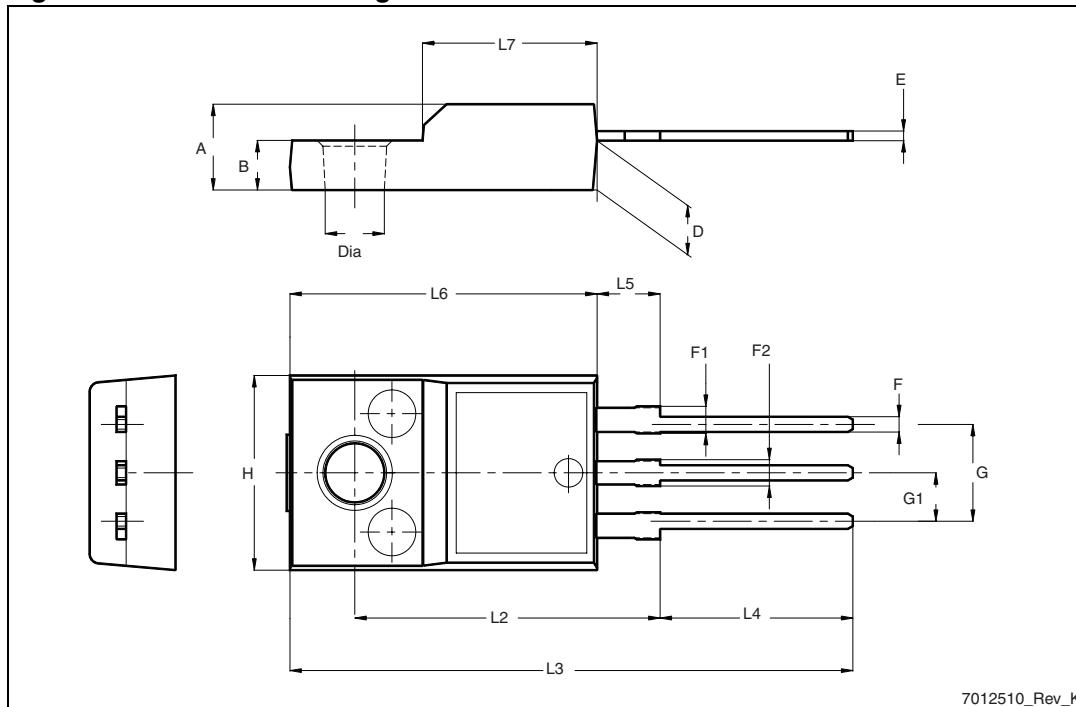


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. TO-220FP mechanical data

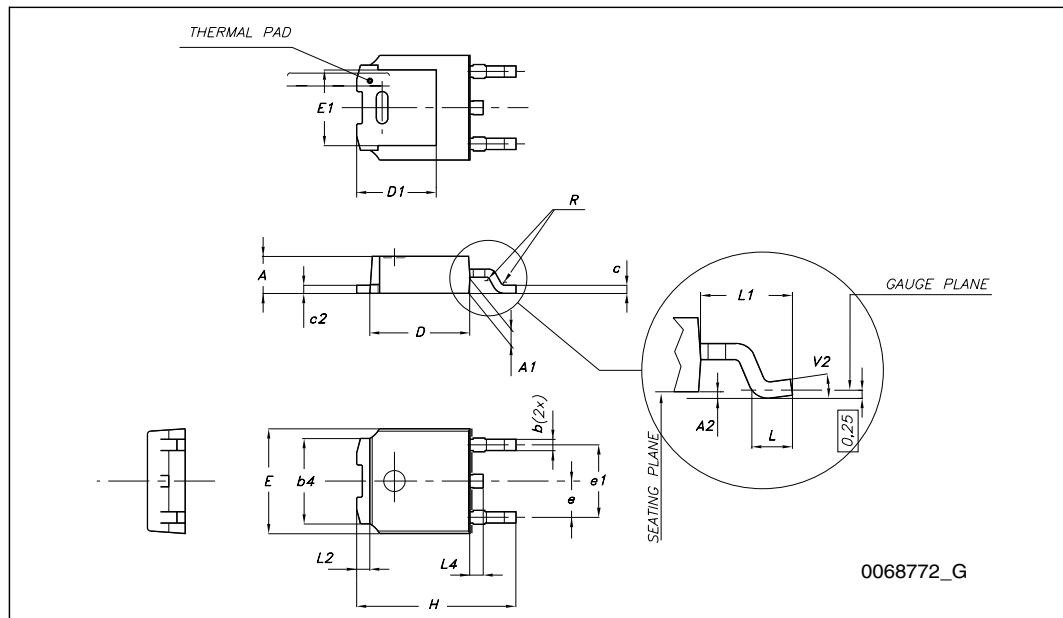
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 23. TO-220FP drawing

7012510_Rev_K

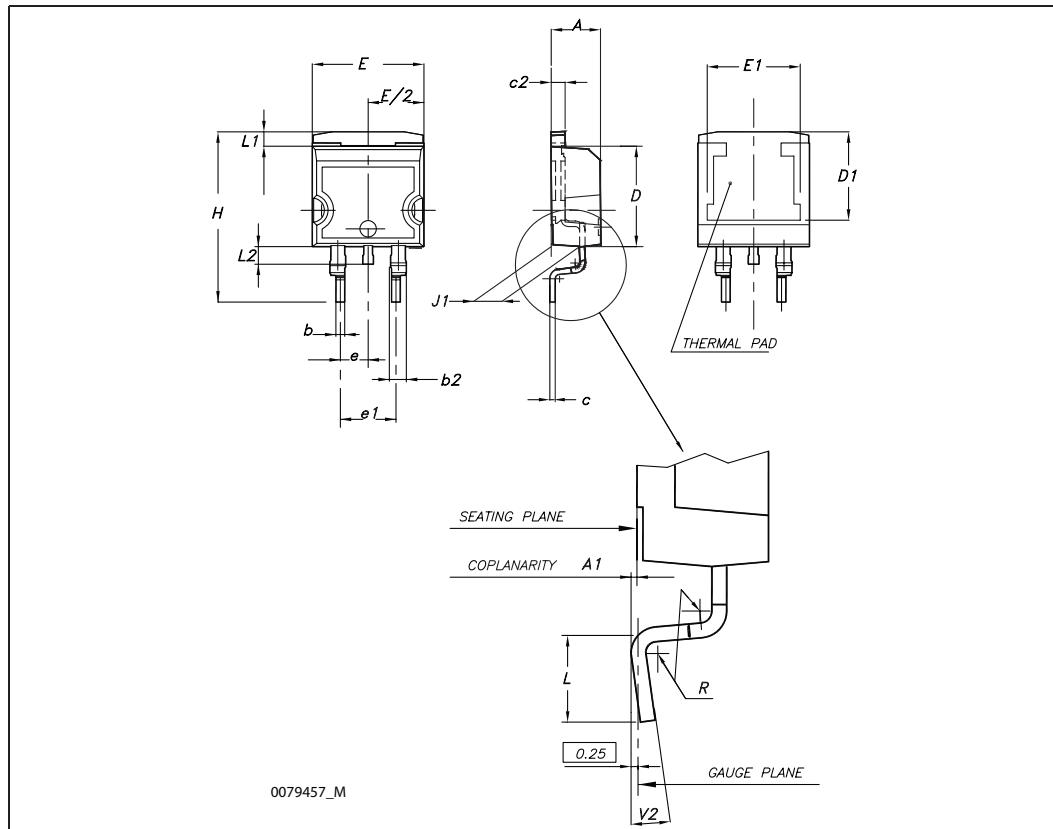
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0 °		8 °



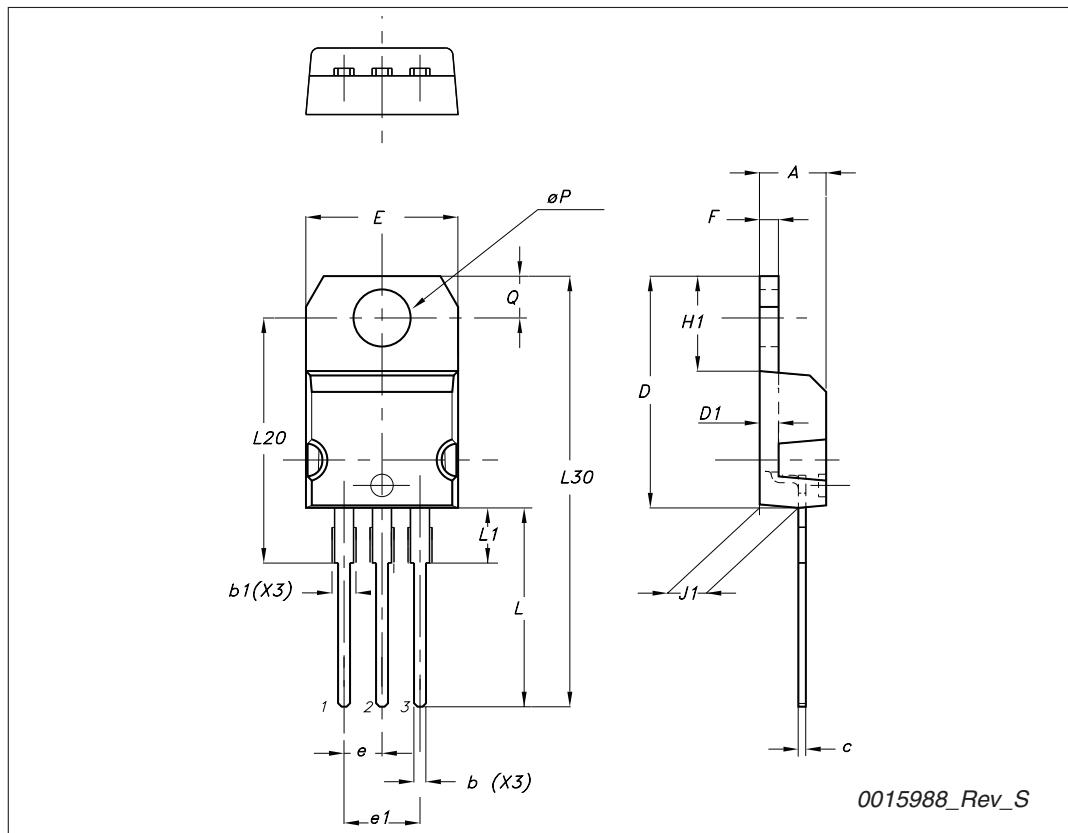
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



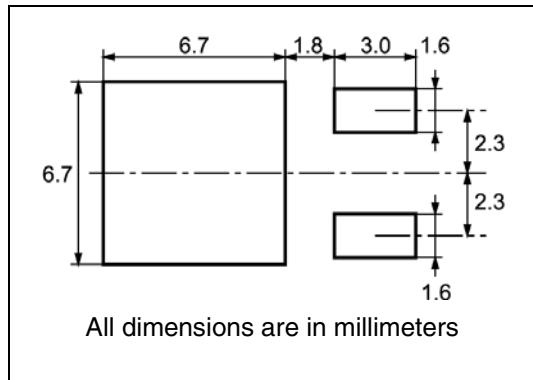
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
$\emptyset P$	3.75		3.85
Q	2.65		2.95

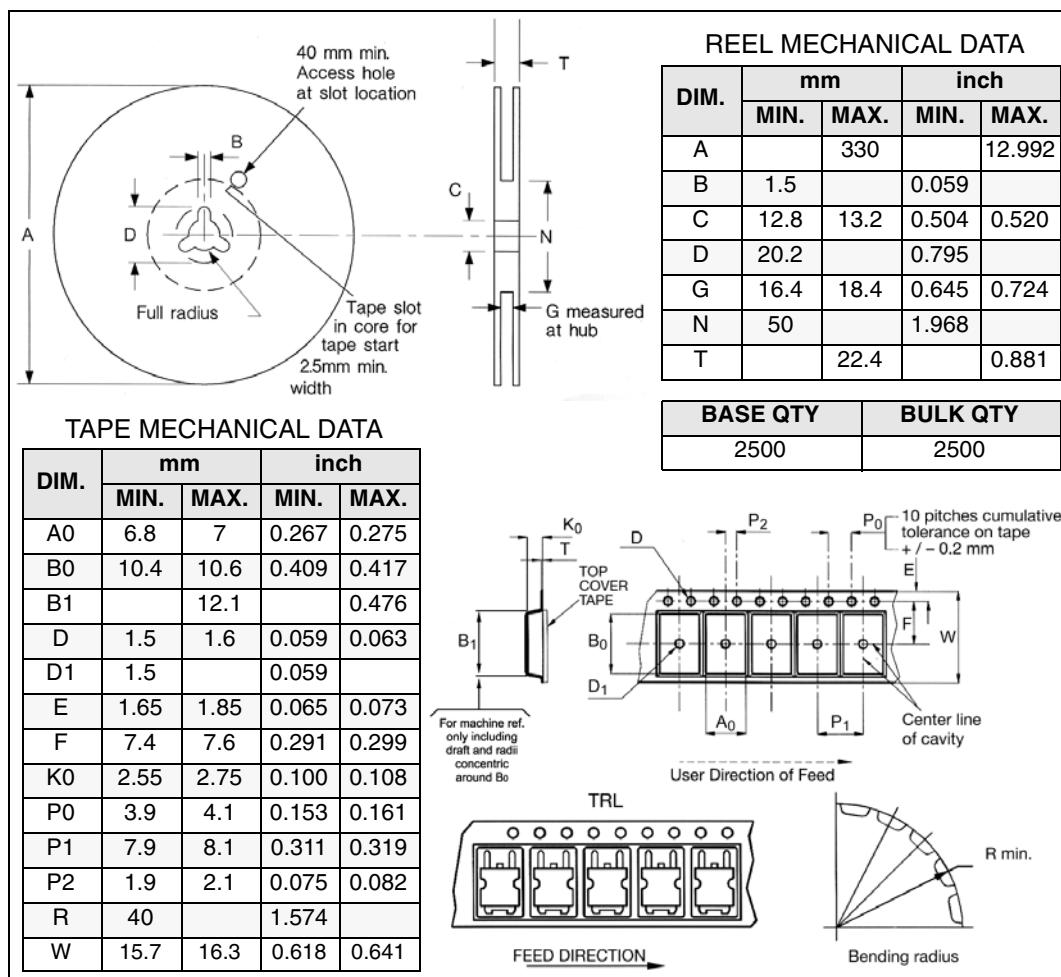


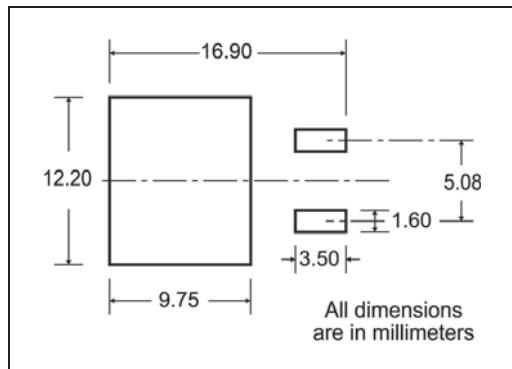
5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



D²PAK FOOTPRINT

TAPE AND REEL SHIPMENT

REEL MECHANICAL DATA			
DIM.	mm	inch	
	MIN.	MAX.	
A		330	12.992
B	1.5		0.059
C	12.8	13.2	0.504
D	20.2		0.795
G	24.4	26.4	0.960
N	100		3.937
T		30.4	1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA				
DIM.	mm	inch		
	MIN.	MAX.		
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

6 Revision history

Table 9. Document revision history

Date	Revision	Changes
26-Nov-2009	1	First release.
02-Dec-2009	2	Inserted table footnote <i>Table 3: Thermal data</i> .
22-Jul-2010	3	Document status promoted from preliminary data to datasheet.

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